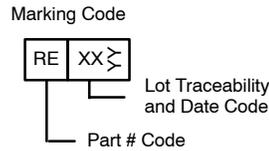
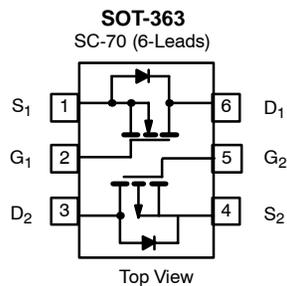




Complementary 20-V (D-S) Low-Threshold MOSFET

PRODUCT SUMMARY			
Channel	V _{DS} (V)	r _{DS(on)} (Ω)	I _D (mA)
N-Channel	20	2.0 @ V _{GS} = 4.5 V	250
		2.5 @ V _{GS} = 2.5 V	150
P-Channel	-20	3.8 @ V _{GS} = -4.5 V	-180
		5.0 @ V _{GS} = -2.5 V	-100



ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)					
Parameter	Symbol	N-Channel	P-Channel	Unit	
Drain-Source Voltage	V _{DS}	20	-20	V	
Gate-Source Voltage	V _{GS}	±8	±8		
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _A = 25 °C	250	-180	mA
		T _A = 70 °C	200	-140	
Pulsed Drain Current	I _{DM}	500	-500		
Maximum Power Dissipation ^a	P _D	T _A = 25 °C	0.20		W
		T _A = 70 °C	0.13		
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 150		°C	

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Maximum Junction-to-Ambient ^a	R _{thJA}	625 (Total)	°C/W

Notes

a. Surface Mounted on FR4 Board, t ≤ 10 sec.

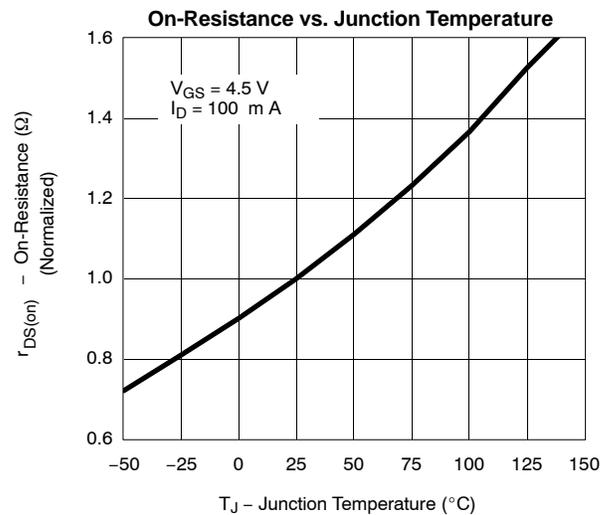
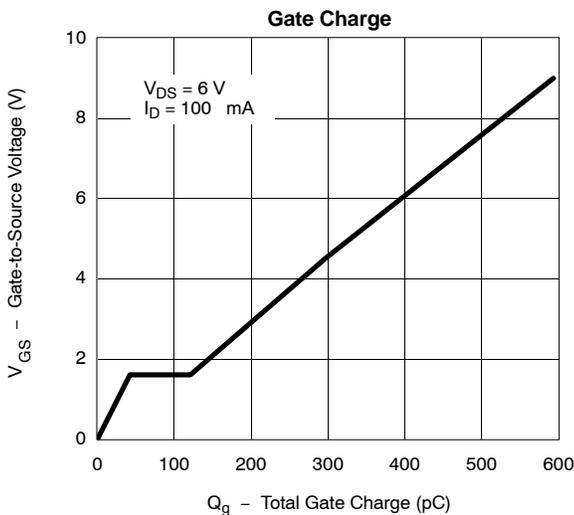
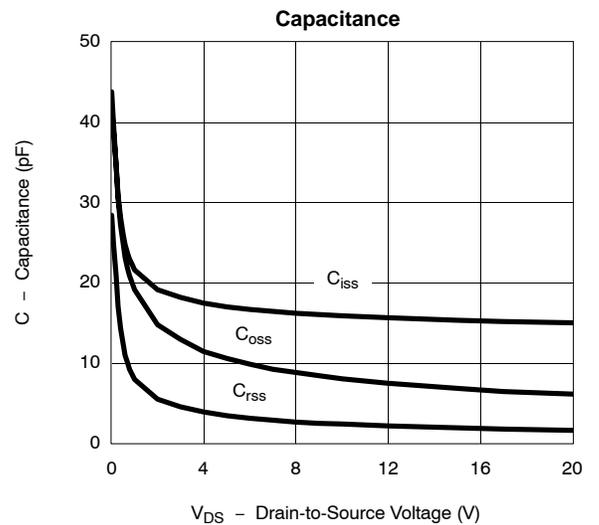
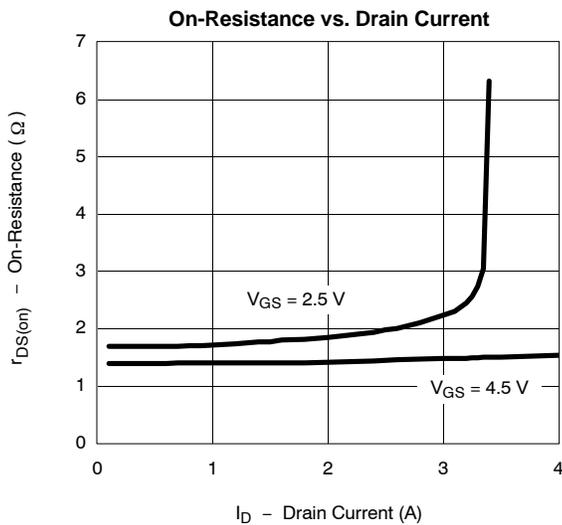
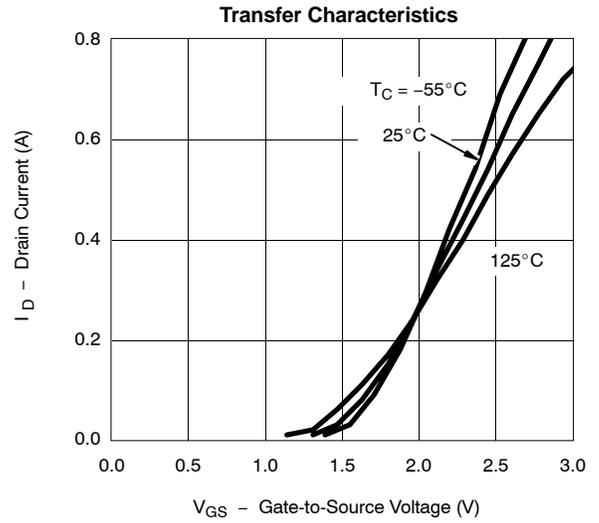
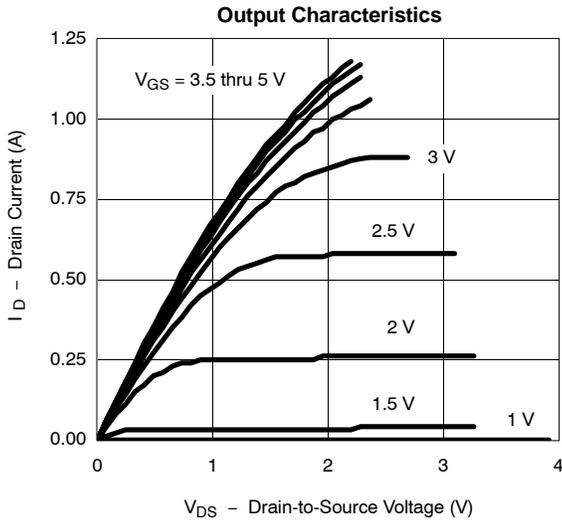
SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit	
Static							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 10 μA	N-Ch	20	24		V
		V _{GS} = 0 V, I _D = -10 μA	P-Ch	-20	-24		
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 50 μA	N-Ch	0.4	0.9	1.5	
		V _{DS} = V _{GS} , I _D = -50 μA	P-Ch	-0.4	-0.9	-1.5	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±8 V	N-Ch		±2	±100	nA
			P-Ch		±2	±100	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V	N-Ch		0.001	100	
		V _{DS} = -20 V, V _{GS} = 0 V	P-Ch		-0.001	-100	
		V _{DS} = 20 V, V _{GS} = 0 V, T _J = 55 °C	N-Ch			1	μA
		V _{DS} = -20 V, V _{GS} = 0 V, T _J = 55 °C	P-Ch			-1	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 2.5 V, V _{GS} = 5.0 V	N-Ch	120			mA
		V _{DS} ≤ -2.5 V, V _{GS} = -5.0 V	P-Ch	-120			
		V _{DS} ≥ 4.5 V, V _{GS} = 8.0 V	N-Ch	400			
		V _{DS} ≤ -4.5 V, V _{GS} = -8.0 V	P-Ch	-400			
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 2.5 V, I _D = 150 mA	N-Ch		1.6	2.5	Ω
		V _{GS} = -2.5 V, I _D = -75 mA	P-Ch		4	5	
		V _{GS} = 4.5 V, I _D = 250 mA	N-Ch		1.2	2.0	
		V _{GS} = -4.5 V, I _D = -180 mA	P-Ch		2.6	3.8	
Forward Transconductance ^a	g _{fs}	V _{DS} = 2.5 V, I _D = 50 mA	N-Ch		150		mS
		V _{DS} = -2.5 V, I _D = -50 mA	P-Ch		200		
Diode Forward Voltage ^a	V _{SD}	I _S = 50 mA, V _{GS} = 0 V	N-Ch		0.7	1.2	V
		I _S = -50 mA, V _{GS} = 0 V	P-Ch		-0.7	-1.2	
Dynamic^b							
Total Gate Charge	Q _g	N-Channel V _{DS} = 5 V, V _{GS} = 4.5 V, I _D = 100 mA P-Channel V _{DS} = -5 V, V _{GS} = -4.5 V, I _D = -100 mA	N-Ch		300	450	pC
Gate-Source Charge	Q _{gs}		P-Ch		300	450	
			N-Ch		25		
Gate-Drain Charge	Q _{gd}		P-Ch		25		
		N-Ch		100			
Input Capacitance	C _{iss}	N-Channel V _{DS} = 5 V, V _{GS} = 0 V P-Channel V _{DS} = -5 V, V _{GS} = 0 V	P-Ch		15		pF
			N-Ch		15		
Output Capacitance	C _{oss}		P-Ch		11		
			N-Ch		11		
Reverse Transfer Capacitance	C _{rss}		P-Ch		5		
			N-Ch		5		
Switching							
Turn-On Time	t _{d(on)}	N-Channel V _{DD} = 3 V, R _L = 100 Ω I _D = 0.25 A, V _{GEN} = 4.5 V, R _g = 10 Ω P-Channel V _{DD} = -3 V, R _L = 100 Ω I _D = -0.25 A, V _{GEN} = -4.5 V, R _g = 10 Ω	N-Ch		7	12	ns
			P-Ch		7	12	
Rise Time	t _r		N-Ch		25	35	
			P-Ch		25	35	
Turn-Off Delay Time	t _{d(off)}		N-Ch		19	30	
			P-Ch		19	30	
Fall Time	t _f		N-Ch		9	15	
			P-Ch		9	15	

Notes

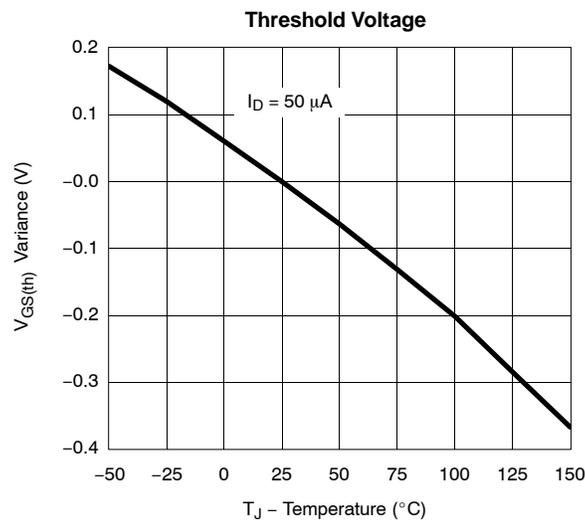
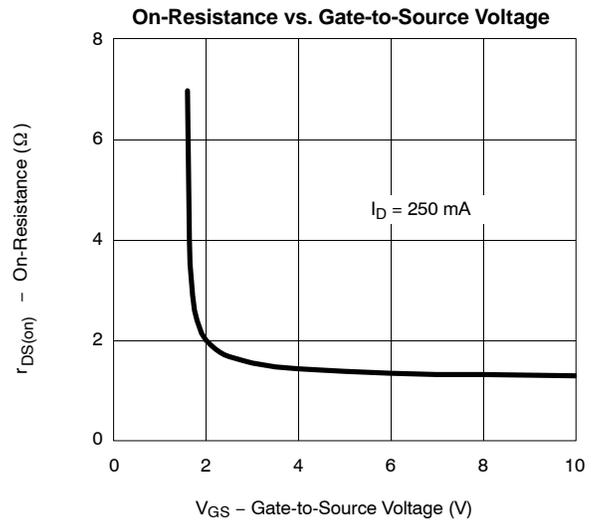
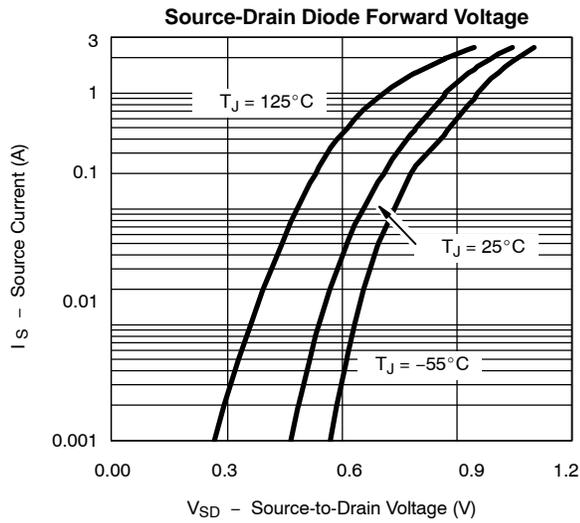
- a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED) N-CHANNEL

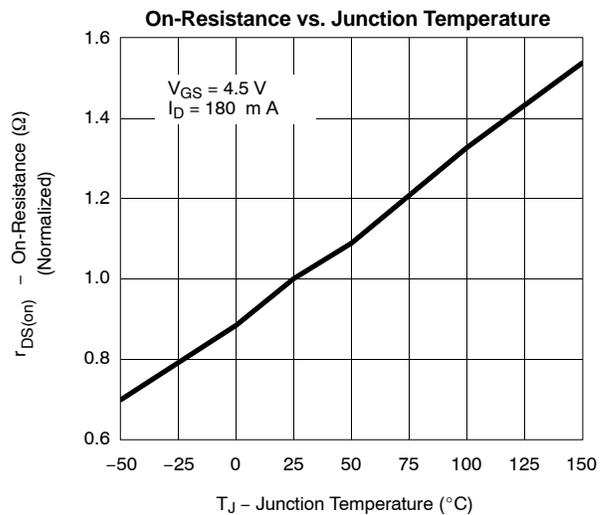
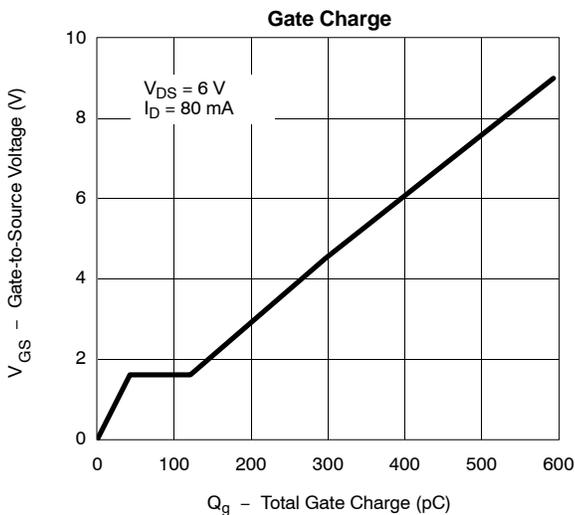
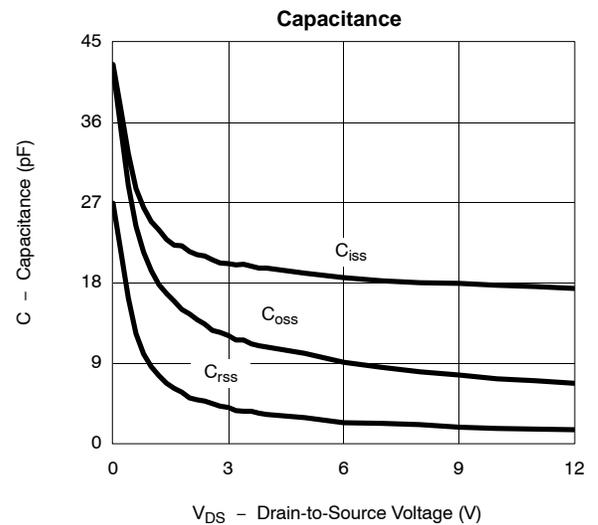
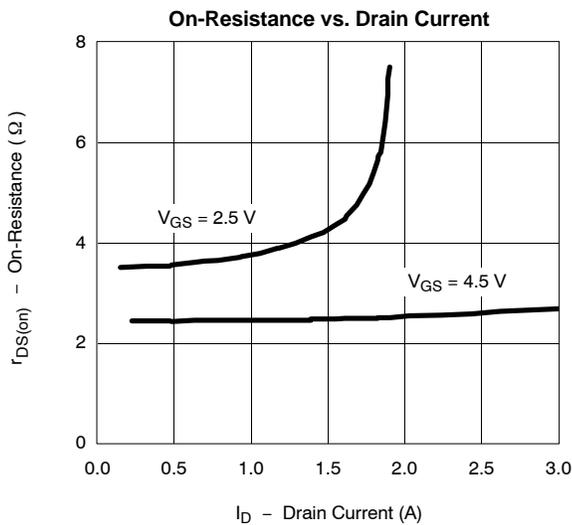
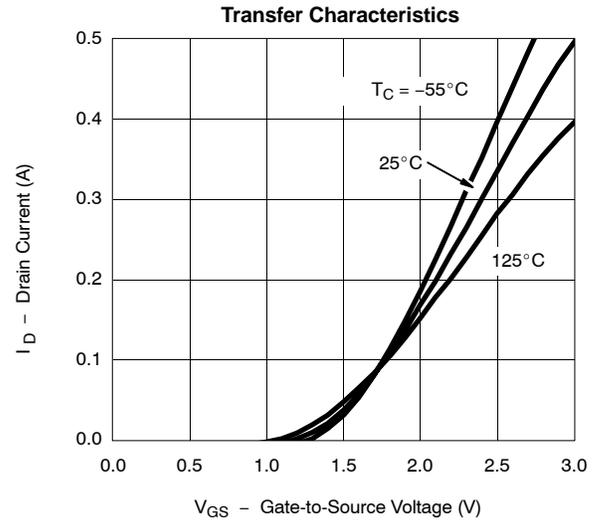
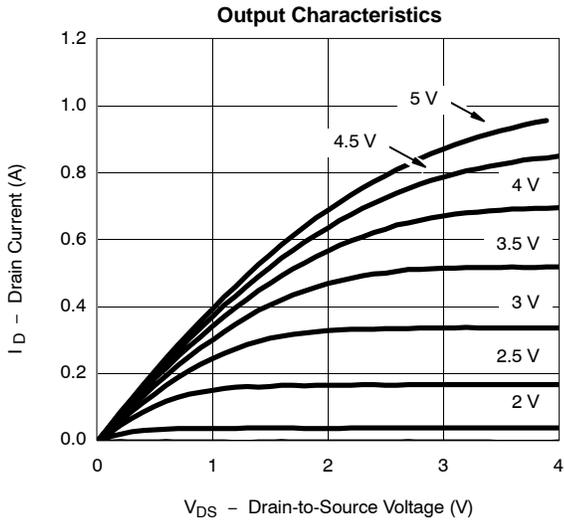


TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED) N-CHANNEL





TYPICAL CHARACTERISTICS (25°C UNLESS NOTED) P-CHANNEL



TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED) P-CHANNEL

